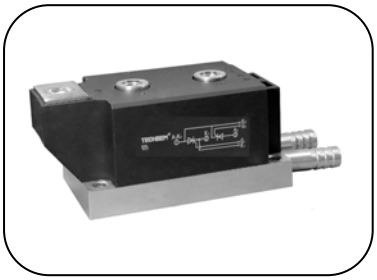


**Features：**

- Isolated mounting base 4000V~
- Pressure contact technology with Increased power cycling capability
- Space and weight saving

**Typical Applications：**

- AC/DC Motor drives
- Various rectifiers
- DC supply for PWM inverter

| $V_{RRM}$,$V_{DRM}$ | Type & Outline | |
|---|---|---|
| 2600V | MTx400-26-406F3 | MFx400-26-406F3 |
| 2800V | MTx400-28-406F3 | MFx400-28-406F3 |
| 3000V | MTx400-30-406F3 | MFx400-30-406F3 |
| 3200V | MTx400-32-406F3 | MFx400-32-406F3 |
| 3400V | MTx400-34-406F3 | MFx400-34-406F3 |
| 3600V | MTx400-36-406F3 | MFx400-36-406F3 |
| 3600V | MT400-36-406F3G | |

MTx stands for any type of **MTC, MTA, MTK**
MFx stands for any type of **MFC, MFA, MFK**

| SYMBOL | CHARACTERISTIC | TEST CONDITIONS | $T_j$(°C) | VALUE | | | UNIT |
|---|---|---|---|---|---|---|---|
| | | | | Min | Type | Max | |
| $I_{T(AV)}$ | Mean on-state current | 180° half sine wave 50Hz Single side cooled, $T_{HS}$=55°C | 125 | | | 400 | A |
| $I_{T(RMS)}$ | RMS on-state current | | | | | 628 | A |
| $I_{DRM}$ $I_{RRM}$ | Repetitive peak current | at $V_{DRM}$ at $V_{RRM}$ | 125 | | | 50 | mA |
| $I_{TSM}$ | Surge on-state current | $V_R$=60%$V_{RRM}$,t=10ms half sine, | 125 | | | 10.5 | kA |
| $I^2t$ | $I^2t$ for fusing coordination | | 125 | | | 551 | $10^3A^2s$ |
| $V_{TO}$ | Threshold voltage | | 125 | | | 0.85 | V |
| $r_T$ | On-state slope resistance | | | | | 0.90 | mΩ |
| $V_{TM}$ | Peak on-state voltage | $I_{TM}$=1200A | 25 | | | 2.85 | V |
| dv/dt | Critical rate of rise of off-state voltage | $V_{DM}$=67%$V_{DRM}$ | 125 | | | 1000 | V/μs |
| di/dt | Critical rate of rise of on-state current | Gate source 1.5A $t_r$ ≤0.5μs Repetitive | 125 | | | 200 | A/μs |
| $I_{GT}$ | Gate trigger current | $V_A$=12V, $I_A$=1A | 25 | 30 | | 200 | mA |
| $V_{GT}$ | Gate trigger voltage | | | 0.8 | | 3.0 | V |
| $I_H$ | Holding current | | | 10 | | 200 | mA |
| $I_L$ | Latching current | | | | | 1000 | mA |
| $V_{GD}$ | Non-trigger gate voltage | $V_{DM}$=67%$V_{DRM}$ | 125 | | | 0.20 | V |
| $R_{th(j-c)}$ | Thermal resistance Junction to case | Single side cooled per chip | | | | 0.100 | °C/W |
| $R_{th(c-h)}$ | Thermal resistance case to heatsink | Single side cooled per chip | | | | 0.040 | °C/W |
| $V_{iso}$ | Isolation voltage | 50Hz,R.M.S,t=1min,$I_{iso}$:1mA(MAX) | | 4000 | | | V |
| $F_m$ | Terminal connection torque(M12) | | | 12 | | 14 | N·m |
| | Mounting torque(M6) | | | 4.5 | | 6 | N·m |
| $T_{vj}$ | Junction temperature | | | -40 | | 125 | °C |
| $T_{stg}$ | Stored temperature | | | -40 | | 125 | °C |
| $W_t$ | Weight | | | | 1580 | | g |
| Outline | 406F3 | | | | | | |

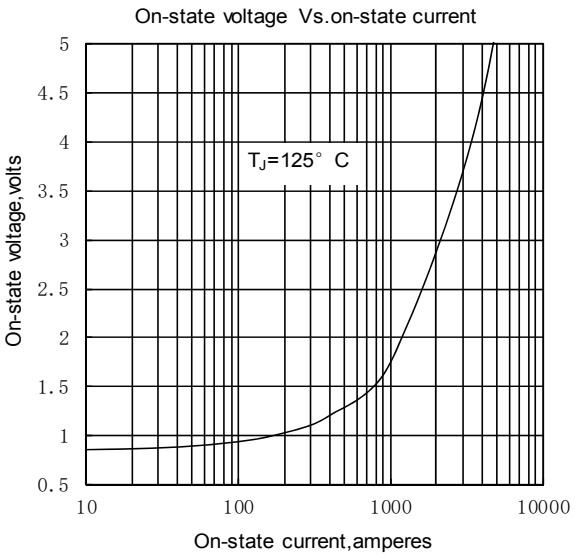



Fig.1

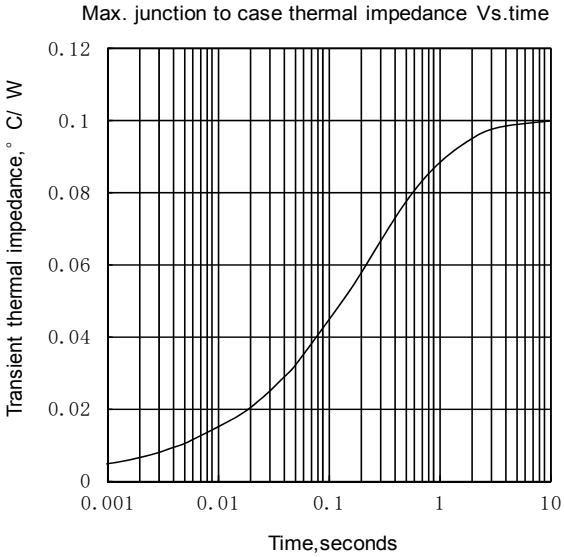



Fig.2

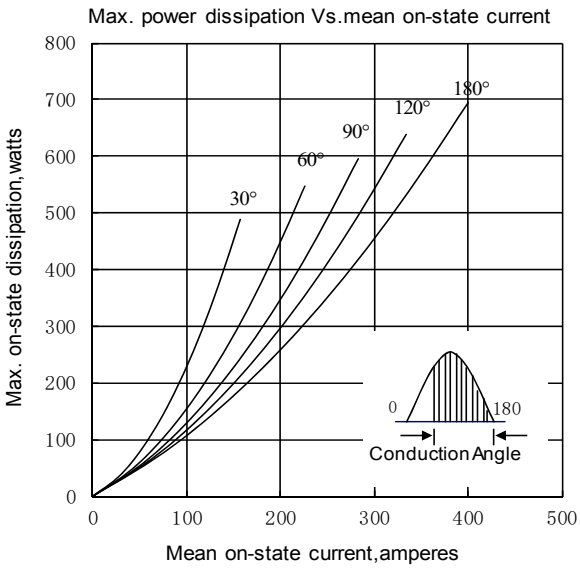



Fig.3

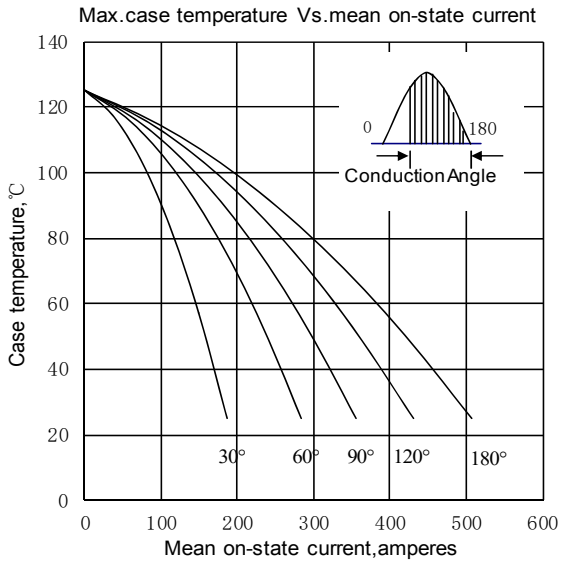



Fig.4

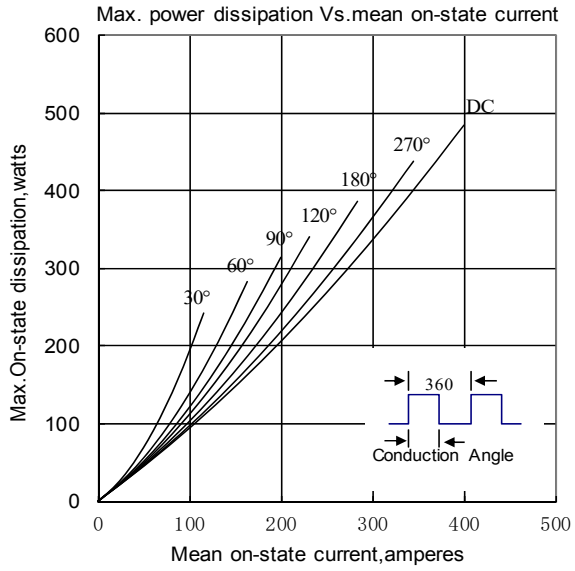



Fig.5

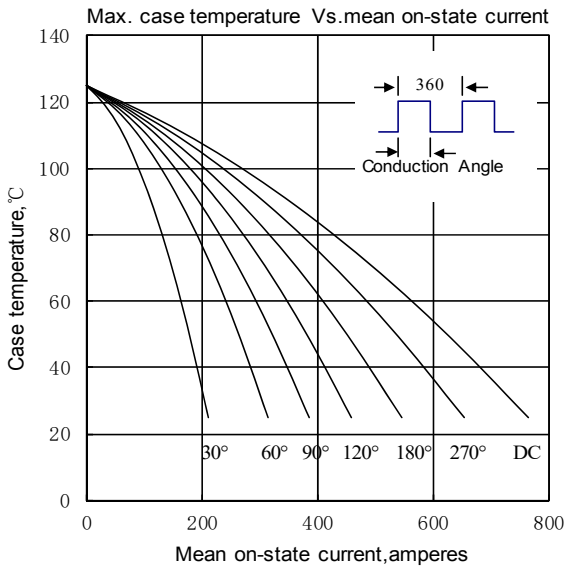



Fig.6

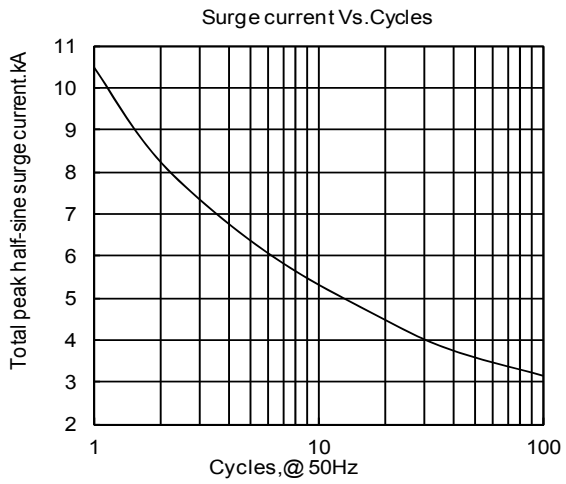



Fig7

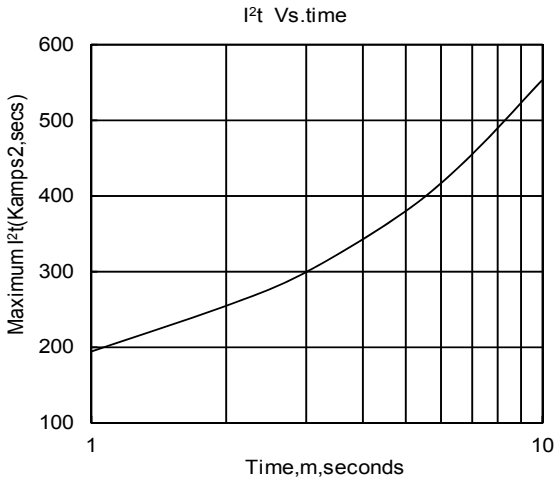



Fig8

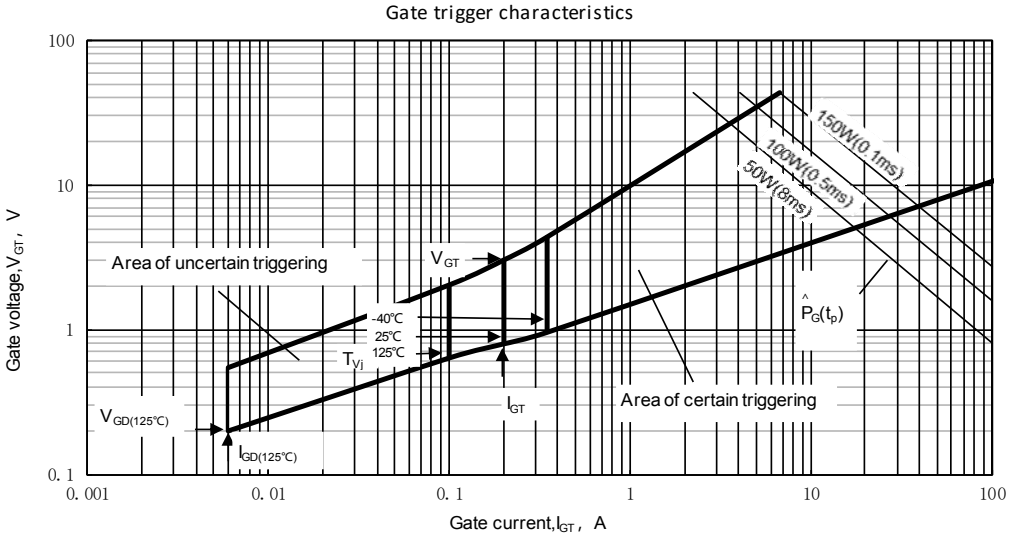
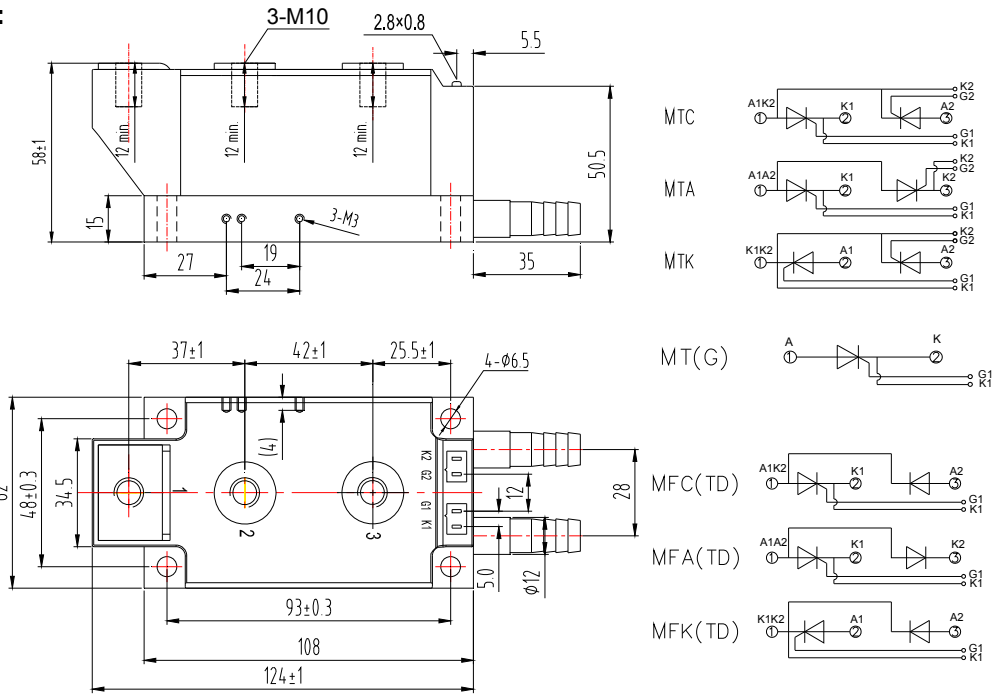



Fig.9

**Outline:**




**Unmarked dimensional tolerance：±0.5mm**

TECHSEM reserves the right to change specifications without notice.